

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 37.60MM×19.00MM OUTLINE
- ✧ THREE DIGIT
- ✧ MONO COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

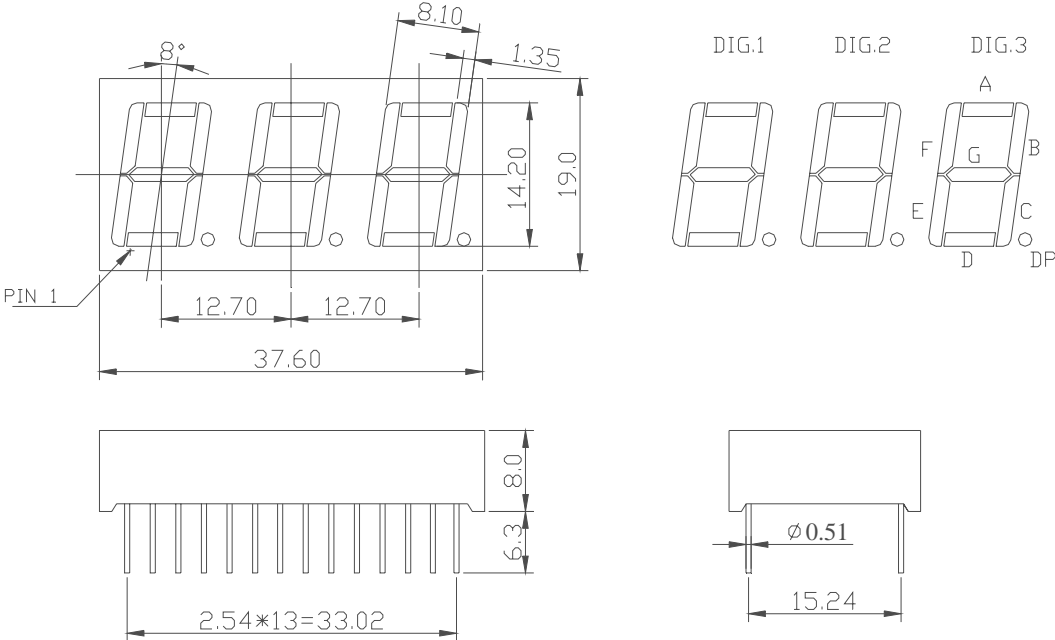
The REC-S5361AG-3 is a 0.56 inches (14.20mm) digit height, 37.60mm×19.0mm outline, single color, three digit numeric display. This display utilizes green LED chips fabricated from GaP epiwafer on GaP substrate grown by liquid phase epitaxy..These devices have black face and white segments.

DEVICE

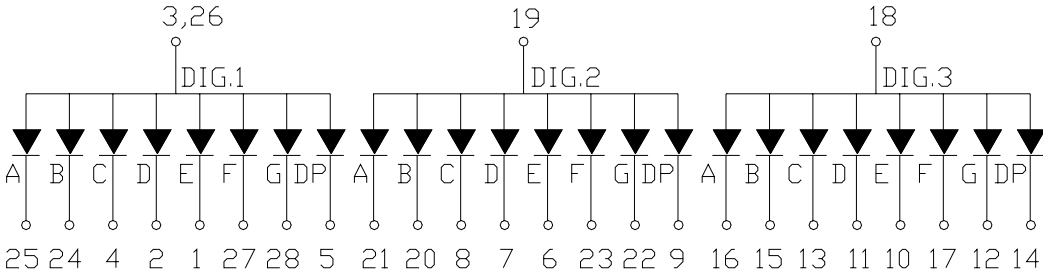
| PART NO. | EMITTING COLOR | DESCRIPTION |
|---------------|----------------|--------------|
| REC-S5361AG-3 | Yellow-Green | Common Anode |

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PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



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PIN CONNECTION

| PIN NO. | CONNECTION | PIN NO. | CONNECTION | PIN NO. | CONNECTION |
|---------|------------------|---------|------------------|---------|-----------------|
| 1 | Cathode E Dig.1 | 11 | Cathode D Dig.3 | 21 | Cathode A Dig.2 |
| 2 | Cathode D Dig.1 | 12 | Cathode G Dig.3 | 22 | Cathode G Dig.2 |
| 3 | Anode Dig.1 | 13 | Cathode C Dig.3 | 23 | Cathode F Dig.2 |
| 4 | Cathode C Dig.1 | 14 | Cathode DP Dig.3 | 24 | Cathode B Dig.1 |
| 5 | Cathode DP Dig.1 | 15 | Cathode B Dig.3 | 25 | Cathode A Dig.1 |
| 6 | Cathode E Dig.2 | 16 | Cathode A Dig.3 | 26 | Anode Dig.1 |
| 7 | Cathode D Dig.2 | 17 | Cathode F Dig.3 | 27 | Cathode F Dig.1 |
| 8 | Cathode C Dig.2 | 18 | Anode Dig.3 | 28 | Cathode G Dig.1 |
| 9 | Cathode DP Dig.2 | 19 | Anode Dig.2 | | |
| 10 | Cathode E Dig.3 | 20 | Cathode B Dig.2 | | |

ABSOLUTE MAXIMUM RATING AT T_A=25° C

| PARAMETER | SYMBOL | MAXIMUM | UNIT |
|--|-----------------|--------------------|------|
| Power Dissipation per Seg. | P _{AD} | 60 | mW |
| Peak Forward Current per Seg. | I _{PF} | 80 | mA |
| Continuous Forward Current per Seg. | I _{AF} | 20 | mA |
| Reverse Voltage per Seg. | V _R | 5 | V |
| Operating Temperature Range, T _{opr} | | - 25° C to + 60° C | |
| Storage Temperature Range, T _{stg} | | - 30° C to + 85° C | |
| Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C | | | |

ELECTRO – OPTICAL CHARACTERISTICS AT T_A=25° C

| PARAMETER | UNIT | MIN | TYPE | MAX |
|--|------|-----|------|-----|
| Luminous Intensity per Seg., I _V (I _F =20mA) | mcd | 7 | 10 | 12 |
| Peak Emission Wavelength, λ _P (I _F =20mA) | nm | | 570 | |
| Special Line Half-Width, Δλ (I _F =20mA) | nm | | 20 | |
| Forward Voltage per Seg., V _F (I _F =20mA) | V | 2.0 | 2.1 | 2.2 |
| Reverse Current per chipSeg., I _R , (V _R =5V) | μA | | | 100 |
| Luminous Intensity Matching Ratio, I _{V-m} (I _F =20mA) | | | | 2:1 |